



UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/523,371	06/21/2005	Jeffrey J. Spiegelman	3194.1026-006	3702
21005	7590	07/13/2010	EXAMINER	
HAMILTON, BROOK, SMITH & REYNOLDS, P.C. 530 VIRGINIA ROAD P.O. BOX 9133 CONCORD, MA 01742-9133			CARRILLO, BIBI SHARIDAN	
			ART UNIT	PAPER NUMBER
			1711	
			MAIL DATE	DELIVERY MODE
			07/13/2010	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

DETAILED ACTION

Claim Rejections - 35 USC § 112

1. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

2. Claim 53 and 55 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention.

3. The limitations of claim 53 constitute new matter not supported by the originally filed specification. Claim 53 is directed to outgassing the organic contaminant by contacting the surface with a purified purge gas comprising O₂ and water. Applicant argues that support can be found in the provisional application 60/ 475145. Specifically, applicant states that the XCDA is passed through a bubbler containing UHP water, and directs applicant's attention to page 15 of the provisional application. Applicant's arguments are unpersuasive. Page 15 of the provisional teaches using a bubbler to "avoid electrostatic buildup". The provisional does not teach using oxygen in combination with water to perform the claimed methods. Therefore the limitations of claim 53 constitute new matter not supported by the originally filed specification or applicant's provisional application. Re claim 55, applicant cites pages 14-15 of the

Art Unit: 1711

Provisional application and relies on the teachings of a moisturizer using a bubbler. Applicant's arguments are unpersuasive for the reasons cited above. Specifically, reference to the bubbler is directed to reducing electrostatic buildup and not directed to outgassing a contaminant from a component in the semiconductor manufacturing process. Additionally, the instant specification, along with the provisional application fails to teach dehumidifying the purified purge gas comprising oxygen, then adding a controlled amount of water to the dehumidified purge gas.

4. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

5. Claim 53 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 53 is indefinite because it is unclear how the "outgassing rate" can be expressed as a concentration value of 1ppt or less. It is unclear what applicant means by the "outgassing rate" reduced is 1ppt or less. Specifically, it is unclear whether applicant intends to outgas the contaminants until the contaminants on the surface are reduced to 1ppt or less. Applicant asserts that the above limitations mean that for every trillion parts of the purge gas provided, one part or less of the organic contaminants outgasses from the surface of the substrate". The examiner is unable of find support in the instant specification of applicant's assertions.

Art Unit: 1711

Claim Rejections - 35 USC § 103

6. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

7. The factual inquiries set forth in *Graham v. John Deere Co.*, 383 U.S. 1, 148 USPQ 459 (1966), that are applied for establishing a background for determining obviousness under 35 U.S.C. 103(a) are summarized as follows:

1. Determining the scope and contents of the prior art.
2. Ascertaining the differences between the prior art and the claims at issue.
3. Resolving the level of ordinary skill in the pertinent art.
4. Considering objective evidence present in the application indicating obviousness or nonobviousness.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Art Unit: 1711

8. Claims 1, 3-4, 8-9, 11, 38, 41, 43-47, and 53-54 are rejected under 35 U.S.C. 103(a) as being unpatentable over Somekh (6427703) in view of Wu et al. (6610123) and further in view of Alvarez Jr. et al. (6391090).

In reference to claims 1, 46, and 53-54, Somekh teaches purging a lithography chamber with water vapor/oxygen containing compound to remove carbon contamination (Figs. 2a, 4) and removing the contamination with a vacuum pump (col. 5, lines 35-40, col. 6, lines 20-25). In reference to the limitations of a purge gas comprising oxygen and water, the teachings of adding water to the purge gas reads on applicant's claimed invention. Additionally, claim 2 of Somekh teaches water vapor doped oxygen compounds. Additionally, it is well known, as evidenced by Kern (Handbook of Semiconductor Wafer Cleaning Technology, 1993, pages 88-89), that oxygen gas contains a small concentration of contaminants such as water. Therefore, one would reasonably expect the oxygen gas of Somekh to include water vapor. Re in reference to the limitations of "outgassing the AMC from the surface of the substrate, col. 8-9 teaches that hydrocarbon gas present in the chamber is oxidized and evacuated from the chamber. Therefore, Somekh teaches outgassing the AMC from the surface of the substrate. Specifically, Somekh teaches driving off gas from the substrate surface.

Somekh teaches the invention substantially as claimed with the exception of the temperature limitation of the purified purge gas. Wu teaches a method of removing contaminants from an enclosure during photolithography using a purge gas (col. 1, lines 5-10, clean dry air). In col. 3, lines 1-10, Wu teaches that the temperature of purge gas

Art Unit: 1711

is set to ambient temperature +/-0.2 degrees centigrade in order not to damage the components present in the enclosure. It would have been obvious to a person of ordinary skill in the art to have modified the method of Somekh, to include the ambient temperature of the purge gas, as taught by Wu et al., for purposes of not damaging the components and also to provide the same ambient conditions as that of the photolithographic system.

Somekh in view of Wu et al. fail to teach purified gases having an AMC concentration level of less than 1ppt.

Alvarez Jr. et al. teach purification of gases used in photolithography in order to reduce the contamination level to 1ppb or lower (col. 7, lines 7-10, col. 8, lines 15-17) such that molecular contaminants on the optical components of the lithography tool is reduced. In col. 8, line 17, Alvarez teaches 100ppt.

It would have been obvious to a person of ordinary skill in the art to have modified the modified method of Somekh to include purification of the lens gases, as taught by Alvarez such that contaminants in the optical components can be avoided. In reference to claims 3-4, and 53, it would have been well within the level of the skilled artisan to repeatedly purify the gases until the desired level of contaminants of less than 1ppt or lower is achieved. Arguably, the skilled artisan would have recognized the advantages of reducing the contaminants in the purified lens gases to values in the ppt range and/or close to zero. In reference to claims 8-9, Somekh fails to teach water in the gas of at least about 100 ppm. Alvarez teaches reducing the amount of water to as

Art Unit: 1711

low as 10-100ppm. In reference to claims 11 and 38, refer to col. 6, lines 1-5 of Somekh.

Re claim 41, refer to the teachings of Wu et al.

In reference to claim 46, Somekh in view of Wu and Alvarez fail to teach the purified gas removing AMC at a faster rate than the same method using nitrogen. However, since Somekh teaches contacting the substrate with water vapor, one would reasonably expect the rate of removal of AMC to be faster than nitrogen having no water present since Somekh is performing the same method steps using the same composition as instantly claimed and recited in the specification. The burden is shifted on applicant to show why the purge gases of Somekh would not produce a faster rate of removal of AMC, especially since the instant specification teaches increasing of the water content increases the removal rate. Re claim 43, refer to col. 6, line 24 of Somekh. Re claims 44-45 and 47, refer to the teachings of Wu et al.

9. Claims 14-15, 40, and 50 are rejected under 35 U.S.C. 103(a) as being unpatentable over Somekh (6427703) in view of Wu et al. (6610123) and Alvarez Jr. et al. (6391090), as applied to claims 1, 3-4, 8-9, 11, 38, 41, 43-47 and 53-54, as described in paragraph 8 above, and further in view of Van Schaik et al. (6724460).

Somekh in view of Wu et al., and Alvarez fail to teach purging with an inert gas. Van Schaik et al. teach in-situ cleaning of optical components for use in a lithographic apparatus. In col. 4, lines 1-22, Van Schaik teach purging with nitrogen. Col. 8, lines 1-5 teaches inert gases also include argon. It would have been obvious to a person of ordinary skill in the art to have modified the modified method of Somekh to include purging with an inert gas, since Van Schaik et al. teach it is conventional to purge with

Art Unit: 1711

an inert gas in order to remove contaminants from the lithographic apparatus. Re claim 40, Van Schaik teaches 20% of oxygen (col. 9, lines 40-45).

10. Claims 1, 3-4, 8-9, 11, 38, 40-41, 43-47, and 51-54 are rejected under 35 U.S.C. 103(a) as being unpatentable over Van Der Net et al. (US2005/0017198) in view of Alvarez Jr. et al. (6391090).

Re claims 1 and 51-54, Van Der Net teaches purging an optical component of a lithographic apparatus to remove contaminants with an ultra high purity gas comprising dry air in combination with moisture (paragraphs 43, 53). Furthermore, paragraph 43 teaches purified clean dry air. The limitations of oxygen are met since it is well known that a major component of air includes oxygen.

Re claims 1, 3-4, Van Der Net et al. fail to teach purification of the purge gas to less than 1 ppb. Alvarez Jr. et al. teach purification of gases used in photolithography in order to reduce the contamination level to 1ppb or lower (col. 7, lines 7-10, col. 8, lines 15-17) such that molecular contaminants on the optical components of the lithography tool is reduced. In col. 8, line 17, Alvarez teaches 100ppt.

It would have been obvious to a person of ordinary skill in the art to have modified the method of Van Der Net to include purification of the lens gases, as taught by Alvarez such that contaminants in the optical components can be avoided. In reference to claims 3-5 and 53, it would have been well within the level of the skilled artisan to repeatedly purify the gases until the desired level of contaminants of less than 1ppb or lower is achieved. Arguably, the skilled artisan would have recognized the advantages of reducing the contaminants in the purified lens gases to values in the ppt

Art Unit: 1711

range and/or close to zero. Re claims 8-9, Van Der Net teaches adjusting the moisture between about 0-100% (paragraph 55). Re claims 11 and 38, refer to paragraph 28, which teaches a wafer. Re claim 40, it is well known and conventional in the art that dry air comprises 20% by volume of oxygen, as further evidenced by Engineering Tool Box. Re claim 41, Van Der Net teaches purified CDA which reads on extra clean dry air. Re claim 46, Van Der Net in view of Alvarez fails to teach the purified gas removing AMC at a faster rate than the same method using ultra high purity nitrogen without water added thereto. However, since Van Der Net in combination with Alvarez teach contacting the substrate with purge gas comprising oxygen, wherein the purge gas has a certain concentration of water present, one would reasonably expect the rate of removal of AMC to be faster than nitrogen having no water present since Van Der Net is performing the same method steps using the same composition as instantly claimed and recited in the specification. The burden is shifted on applicant to show why the purge gases of Van Der Net, having a concentration of water present therein, would not produce a faster rate of removal of AMC. Re claim 43, refer to paragraph 43 of Van Der Net. Re claims 44-45, and 47, paragraph 49 teaches ambient conditions, which are no higher than 80C or no higher than 50C.

11. Claims 14-15 and 50 are rejected under 35 U.S.C. 103(a) as being unpatentable over Van Der Net et al. (US2005/0017198) in view of Alvarez Jr. et al. (6391090), as applied to claims 1, 3-4, 8-9, 11, 38, 40-41, 43-47, and 51-54, as described in paragraph 10 above, and further in view of Van Schaik et al. (6724460).

Art Unit: 1711

Van Der Net in view of Alvarez fail to teach purging with an inert gas. Van Schaik et al. teach in-situ cleaning of optical components for use in a lithographic apparatus. In col. 7, lines 56-65, Van Schaik teach purging with nitrogen. Col. 8, lines 1-5 teaches inert gases also include argon. It would have been obvious to a person of ordinary skill in the art to have modified the modified method of Van Der Net et al. to include purging with an inert gas, since Van Schaik et al. teach it is conventional to purge with an inert gas in order to remove contaminants from the lithographic apparatus.

12. Claims 52-53 are rejected under 35 U.S.C. 103(a) as being unpatentable over Van Schaik et al. (6724460) in view of Alvarez Jr. et al. (6391090).

Van Schaik et al. teach in-situ cleaning by purging a lithographic apparatus with a purge gas composition to remove hydrocarbon contamination. In col. 7, lines 23-25, Van Schaik teaches the purge gas may contain one or a mixture of oxygen containing species selected from water, nitrogen oxides and oxygen containing hydrocarbons. Furthermore, col. 7, lines 40-45 teaches the addition of molecular oxygen and water to the purge gas. Also the abstract teaches molecular oxygen. Therefore, Van Schaik teaches a mixture of water and nitrogen oxides, which reads on applicant's claim language of water in combination with oxygen.

Van Schaik fails to teach purification of the purge gas to less than 1 ppm. Alvarez Jr. et al. teach purification of gases used in photolithography in order to reduce the contamination level to 1ppb or lower (col. 7, lines 7-10, col. 8, lines 15-17) such that

Art Unit: 1711

molecular contaminants on the optical components of the lithography tool is reduced. In col. 8, line 17, Alvarez teaches 100ppt.

It would have been obvious to a person of ordinary skill in the art to have modified the method of Van Schaik to include purification of the lens gases, as taught by Alvarez such that contaminants in the optical components can be avoided. In reference to “conditions that do not chemically change or alter the AMC”, the limitations are met by Van Schaik because Van Schaik teaches removing hydrocarbons and other contaminants from the surface of the optical component. Van Schaik teaches that the purge gas is chemically altered by forming radicals, however the contaminants are removed and not chemically altered. Therefore, the limitations are met by the prior art. Re claim 53, the limitations are met in view of the indefiniteness as described above.

Double Patenting

13. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the “right to exclude” granted by a patent and to prevent possible harassment by multiple assignees. A nonstatutory obviousness-type double patenting rejection is appropriate where the conflicting claims are not identical, but at least one examined application claim is not patentably distinct from the reference claim(s) because the examined application claim is either anticipated by, or would have been obvious over, the reference claim(s). See, e.g., *In re Berg*, 140 F.3d 1428, 46 USPQ2d 1226 (Fed. Cir. 1998); *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) or 1.321(d) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent either is shown to be commonly owned with this application, or claims an invention made as a result of activities undertaken within the scope of a joint research agreement.

Art Unit: 1711

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

14. Claims 1, 3-4, 11, 14-15, 38, 40-41, 43-45, 50 and 52-54 are rejected on the ground of nonstatutory obviousness-type double patenting as being unpatentable over claims 1-4, 7, 9-14, and 20-23 of U.S. Patent No. 7189291. Although the conflicting claims are not identical, they are not patentably distinct from each other because the claims are directed to removing contaminants from a substrate using a purified purge gas comprising oxygen.

15. Claims 1, 3, 8, 11, 14-15, 38, 41, 43, 46, and 50-54 are rejected on the ground of nonstatutory obviousness-type double patenting as being unpatentable over claims 1, 6, 11-21, and 23-24 of U.S. Patent No. 7377982. Although the conflicting claims are not identical, they are not patentably distinct from each other because the claims are directed to removing contaminants from a substrate using a purified purge gas comprising water.

Response to Arguments

16. The rejections of the claims, under 112, first and second paragraph are maintained for the reasons set forth above. The examiner maintains the position that the Provisional Application 60/475145 does not provide support for claims 53-54, for the reasons recited above.

17. Applicant argues that the claimed method desorbs contaminants from equipment surfaces more efficiently than nitrogen. Applicant further cites that XCDA has an elution times of about 6 hours and 20 minutes, as compared to nitrogen, with an elution

Art Unit: 1711

time of 7 hours. Applicant's arguments are not persuasive for the following reasons.

Applicant's arguments are not commensurate in scope with the instantly claimed invention. Furthermore, the examiner sees no statistical difference between a value of about 6 hours 20 minutes of XCDA, as compared to 7 hours for nitrogen.

18. Applicant argues that Somekh fails to teach outgassing the AMC from the surface of the substrate. Applicant's argues that outgasses means to drive off the gas from a solid. Applicant's arguments are unpersuasive because Somekh specifically teaches removing hydrocarbon gas from the substrate surface.

19. Re Somekh in view of Alvarez Jr. et al. and Wu et al., applicant continues to argue that the prior art references fail to teach contacting the substrate with a purified purge gas at a temperature of about 20-100C. Applicant argues that the secondary reference of Wu fails to cure the deficiency of the claimed temperature limitation. Specifically, applicant argues that the reference to "ambient" refers to the temperature surrounding the mask and not the temperature of the purge gas. Applicant's arguments are unpersuasive. Wu specifically teaches in col. 2, lines 55+ to col. 3, lines 1-5 that the temperature of the purge gas is chosen to be the "same as the ambient temperature" in the vicinity of the mask 240 in the stepper. Specifically, Wu teaches ambient temperature of the purge gas. It is well known in the cleaning art, as evidenced by Heller et al., (U.S. Patent 4276368), that ambient temperature refers to room temperature. Since room temperature is within the range of 20-25C, the limitations are met by the prior art of Wu. As further evidenced by the prior art, Hamada et al.

Art Unit: 1711

(6652667, col. 14, lines 12+) teaches that ambient or room temperature refers to about 20-25C.

20. In response to applicant's argument that the examiner's conclusion of obviousness is based upon improper hindsight reasoning, it must be recognized that any judgment on obviousness is in a sense necessarily a reconstruction based upon hindsight reasoning. But so long as it takes into account only knowledge which was within the level of ordinary skill at the time the claimed invention was made, and does not include knowledge gleaned only from the applicant's disclosure, such a reconstruction is proper. See *In re McLaughlin*, 443 F.2d 1392, 170 USPQ 209 (CCPA 1971). Wu teaches ambient temperature and the examiner has cited several prior art references to teach that it is well known in the art, as evidenced by Heller and Ahmadi et al., that ambient temperature refers to applicant's claimed temperature range.

21. Applicant argues that the skilled artisan would not combine the teachings of Somekh in view of Wu because the purging method of Somekh would require higher temperatures in order for the oxidation process to occur. Applicant cites Exhibits A and B, as previously presented. As previously discussed in the last Office Action, the Exhibits are not persuasive because they are directed to different methodologies. Specifically, Exhibit A is incomplete because it only includes a technical discussion to an article directed to catalyst cartridges. Exhibit B is directed to a gravimetric method. Both exhibits are directed to different methods which are unrelated to a photolithographic process and a purge gas. Furthermore, applicant's arguments are unpersuasive because they are not commensurate in scope with the instantly claimed

Art Unit: 1711

invention. The claims are not limited to a particular contaminant, flow rate, or other conditions cited in the exhibit. Applicant's arguments are unpersuasive because they are not commensurate in scope with the instantly claimed invention. Specifically, the claims are not limited to the removal of carbon deposits or the removal of hydrocarbon gas. Furthermore, Somekh teaches that the purge gas can be activated by similar methods, and therefore not limited to only microwave or plasma source. Furthermore, there is no suggestion that thermal activation of Somekh would require a temperature outside of applicant's claimed range. Applicant argues that the examiner has not provided any reason or factual evidence showing that the oxidation of carbon deposits occurs within the claimed range of 20-100C. Applicant is directed to Inoue et al. (5786042, col.2, lines 55-60), which teaches that it is well known in the art to oxidize carbon in contact with oxygen at room temperature and in the presence of an oxidizing agent such as ozone. Applicant argues that Inoue fails to teach oxidation with O₂. Applicant argues that free oxygen is not the same as O₂. Applicant's arguments are unpersuasive. Applicant is directed to Matheson (6146531, col. 1, lines 40-45) which teaches that free oxygen is the same as O₂.

22. Re claims 14-15 and 50, applicant argues that Van Schaik fails to teach purging with an inert gas such as nitrogen. Applicant is directed to col. 7, lines 55-65, and col. 8, lines 1-5, which teaches purging with an inert gas. Furthermore, it is well known in the art to purge with an inert gas to remove contaminants from a substrate surface.

Art Unit: 1711

23. Applicant argues that Van Schaik teaches 20% of the oxygen species, but fails to teach 20% by volume. Applicant is directed to col. 8, lines 14-15 which teaches that the concentrations are expressed as volume percent.

24. Applicant argues that the prior art of Van Der Net is not applicable as prior art because the filing date is after the effective filing date of the instant application.

Applicant specifically argues that claims of the present application are supported by the U.S. Provisional application No 60/475145 with a filing date of 6/2/03, which is before the filing date of 7/21/03 of the Van Der Net reference. Applicant's arguments are not persuasive because the claimed invention is not supported by the provisional application, and therefore the effective filing date of the instantly claimed invention is 10/10/03, after the filing date of the Van Der Net reference. Specifically, the limitations of the purge gas comprising oxygen and water are not supported by the provisional application for the reasons recited above. The reference to the addition of water, as described in the provisional application, is directed to the reduction of static electricity.

25. Re Van Der Net in view of Alvarez, applicant argues that the skilled artisan would not have been motivated to combine the references because Van Der Net teaches adding moisture and Alvarez states the importance of removing water. Specifically, applicant argues that the examiner has failed to consider the prior art reference as a whole. Applicant argues that paragraph 55 of Van Der Net merely states that the system has the capability to adjust the relative humidity. Applicant's arguments are unpersuasive because paragraph 55 of Van Der Net teaches that the purge gas mixture can contain have a relative humidity between 0-100% and therefore the purge gas of

Art Unit: 1711

Van Der Net could contain, as one embodiment, no moisture or water having concentration amounts in the ppm range. Based on the teachings of Van Der Net, the relative humidity of the purge gas can be adjusted between 0-100%. Specifically, Van Der Net teaches that the amount of moisture (relative humidity) present in the purge gas can be adjusted between 0-100%. The examiner maintains the position that Van Der Net teaches adjusting the moisture, such that the purge gas can have an amount of moisture within the range of 0-100%. Alvarez clearly teaches that the lens gases conventionally have water present in the ppm range. Therefore, as one possible embodiment the purge gas of Van Der Net could have water in the ppm range.

26. Re claims 52 and 53, applicant argues that Van Schaik fails to teach outgassing the AMC from the surface of the substrate. Specifically, applicant argues that Van Schaik teaches a reaction with the contaminants. Applicant's arguments are unpersuasive for the following reasons. Applicant is directed to col. 7, lines 20-22 which teaches the removal of hydrocarbons and other contaminant particles from the surface of the optical component. Furthermore, applicant's claim language of comprising is open-ended to include additional process steps and/or ingredients.

27. The double patenting rejections are maintained. No new arguments have been presented.

28. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

Art Unit: 1711

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Sharidan Carrillo whose telephone number is 571-272-1297. The examiner can normally be reached on M-W, F 6:30-5:00pm, alternating Thursday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Barr can be reached on 571-272-1414. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Sharidan Carrillo
Primary Examiner
Art Unit 1711

/Sharidan Carrillo/
Primary Examiner, Art Unit 1711

bsc